



# AMP2017B SOLID STATE HIGH POWER AMPLIFIER

## FEATURES

- Rack mounted system
- Class A/AB linear LDMOS design
- Instantaneous ultra-wide bandwidth
- Designed for broadband EMI/RFI, Lab, Comm. and EW applications
- Suitable for CW, pulse and all single channel modulation standards
- Built-in protection circuits
- High reliability and ruggedness



## ELECTRICAL SPECIFICATIONS: 25°C, 50Ω

Parameter	Specification	Notes
Operating Frequency Range	400 - 1000 MHz	
Power Output @ Psat	125 Watt Min	CW
Power Output @ P1dB	80 Watt Typ	
Power Gain	51 dB Min	Pin=0dBm for nominal Pout
Power Gain Flatness	3.0 dB p-p Max	Constant input power
Input Return Loss	-10 dB Max	
2-Tone Intermodulation (IMD)	-30 dBc Typ	40dBm/Tone, Δ = 1MHz
Harmonics	-20 dBc Typ	At rated output power
Spurious	-60 dBc Max	Non-harmonics
Operating Voltage	100 - 240 VAC±10%	50/60 Hz
Power Consumption	1000 Watt Max	At rated Pout
Input Power Protection	+8 dBm Max	<10 Sec without damage
Load VSWR Protection	5 : 1 Max	<1 Minute at rated Pout

## ENVIRONMENTAL CHARACTERISTICS

Parameter	Specification	Notes
Operating Ambient Temperature	0 to +50°C	
Storage Temperature	-40 to +85 °C	
Relative Humidity	5 to 95 %	Non-condensing

## MECHANICAL SPECIFICATIONS

Parameter	Specification	Notes
Dimensions W x H x D	430 x 133 x 560 mm	3U - Excluding handles
Weight	20 kg.	
RF Connectors In/Out	Type-N Female	Front or rear panel
AC Power / Interface Connector	IEC 60320-C14 / 9-Pin D-Sub	
Cooling	Built in Fan Cooling	Variable speed
<b>OPTIONAL:</b> Digital Monitor & Control FWD, REV, VSWR, GAIN, ALC, V & I, TEMP	Ethernet RJ-45 TCP/IP, RS422/485, USB Optional GPIB Interface	Optional Remote Bluetooth application

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## OUTLINE DRAWING

